

--38.(once amended) [An] The electroluminescent device of claim 22, wherein both hole-transporting layer and CNC layer is substituted by a viscous composite comprising of CNCs, hole-transporting organic semiconductors, oxidative agents, soluble salts and [low] lower than atmospheric vapor pressure viscosity-modifying agents

39. [An] The electroluminescent device of claim 38, wherein viscous composite is contained within appropriate openings realized between [said elastomeric] spacers, which are made of hole transporting viscous composite.

40. [An] The electroluminescent device of claim 39, wherein the holes in said [elastomeric] spacers are filled with said viscous composite with distinct emission characteristics.

41. [An] The EL device as described in claim 40, wherein the viscous composites [is] are introduced by [a] method selected from the group consisting of [such as] screen-printing and ink-jet printing.

42. An [electroluminescent (EL) device, of claim 1, where in *p-n* junction is replaced by an] *n-p-n* junction electroluminescent device comprising successive layers of:

an *n*-type silicon layer on an insulator substrate, comprising thin doped Si n/n^+ regions separated by insulating regions, such as SiO₂, wherein said *n*⁺ regions are contacted to form bottom electrodes;

a thin-layer of Si allowing for further epitaxial growth;

an *n*⁺-type Si layer, [the said layer has] having addressing contact electrodes;

a thin (about 10 nm) SiO₂ layer [is deposited], which is deposited and patterned with a pitch of about 0.1microns;

a *p*-Si layer forming nanotips;

an *n*-type wide energy gap layer selected from [a] the group of semiconductors [such as] consisting of: Zn_aMg_{1-a}Se, Zn_aMg_{1-a}S, Zn_aMg_{1-a}S_bSe_{1-b}, Zn_aBe_{1-a}S_bSe_{1-b}, Al_cGa_{1-c}N, ZnMgBeSe, AlInN, stacked on the layer comprising of nanotips;

a layer comprising of cladded quantum dots;

an *n*-type [wider] wide gap semiconductors layer selected from the semiconductors consisting of: Zn_aMg_{1-a}Se, Zn_aMg_{1-a}S, Zn_aMg_{1-a}S_bSe_{1-b}, Zn_aBe_{1-a}S_bSe_{1-b}, Al_cGa_{1-c}N, ZnMgBeSe, AlInN; and

a layer forming contact electrodes, wherein said set of electrodes are appropriately biased and addressed to create a two-dimensional display.